

ABSTRACT OF THE DISCLOSURE

Setting values of a light exposure and a focus position are set in an exposure process for forming a pattern on a substrate. Pseudo measured dimensions of the pattern are calculated with respect to each of the combinations of the setting values. ED-trees and a plurality of margin curves are calculated based on the pseudo measured dimensions with respect to each of the combinations. A dispersion of a tolerance of the light exposure of the margin curves is calculated at a depth of focus corresponding to a maximum difference in height of the substrate.